

# isc N-Channel Mosfet Transistor

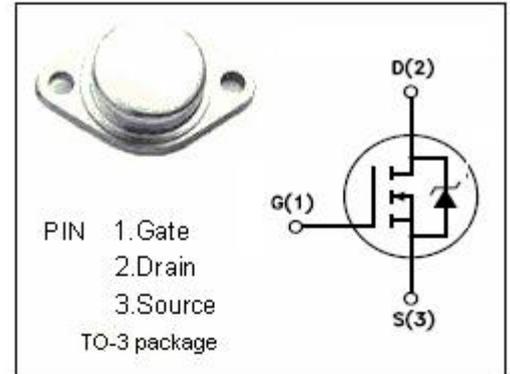
# IRF441

## FEATURES

- $V_{GS}$  Rated at  $\pm 20V$
- Silicon Gate for Fast Switching Speeds
- $I_{DSS}, V_{DS(on)}, SOA$  and  $V_{GS(th)}$  specified at Elevated temperature
- Rugged
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

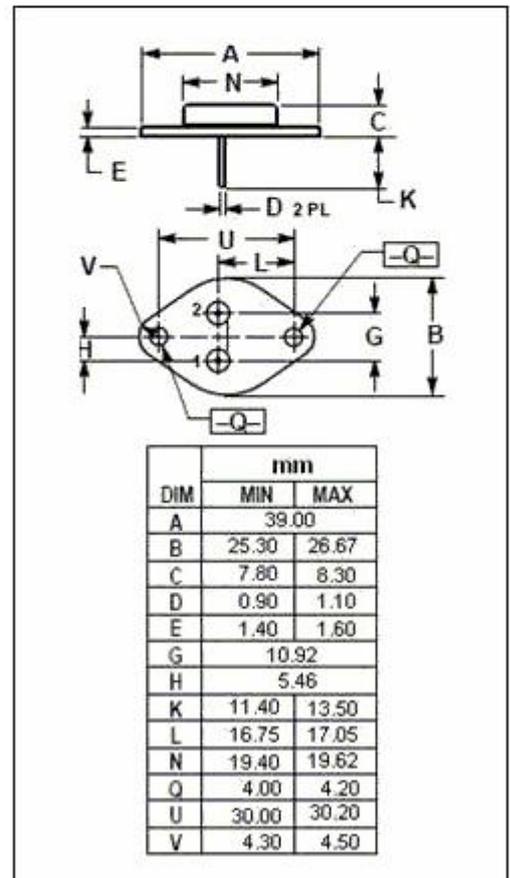
## APPLICATIONS

- Designed especially for high voltage, high speed applications, such as off-line switching power supplies, UPS, AC and DC motor controls, relay and solenoid drivers.



## ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	450	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $TC=25^\circ C$	8	A
$I_{DM}$	Drain Current-Single Pulsed	32	A
$P_{tot}$	Total Dissipation@ $TC=25^\circ C$	125	W
$T_j$	Max. Operating Junction Temperature	-55~150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ C/W$
$R_{th j-A}$	Thermal Resistance, Junction to Ambient	60	$^\circ C/W$

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## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> =0.25mA	450			V
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.25mA	2.0		4.0	V
R <sub>DS(ON)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =4A			0.85	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> =±20V; V <sub>DS</sub> =0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =450V; V <sub>GS</sub> =0			25	μA
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =8A; V <sub>GS</sub> =0			2.0	V
G <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V; I <sub>D</sub> =4A	4.0			S
t <sub>d(on)</sub>	Turn-on Delay Time	I <sub>D</sub> =4A; V <sub>DD</sub> =220V; R <sub>GS</sub> =4.7 Ω; V <sub>GS</sub> =10V			35	ns
t <sub>r</sub>	Rise Time				15	
t <sub>d(off)</sub>	Turn-off Delay Time				90	
t <sub>f</sub>	Fall Time				30	

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